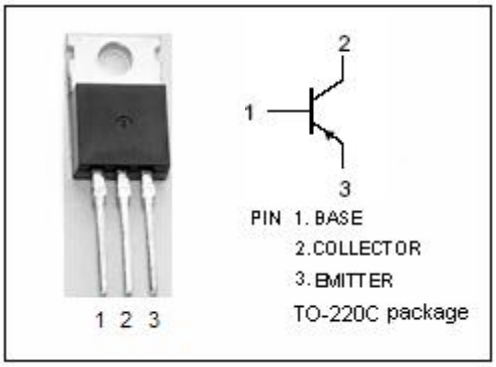
isc Silicon PNP Power Transistor 2SA770



DESCRIPTION

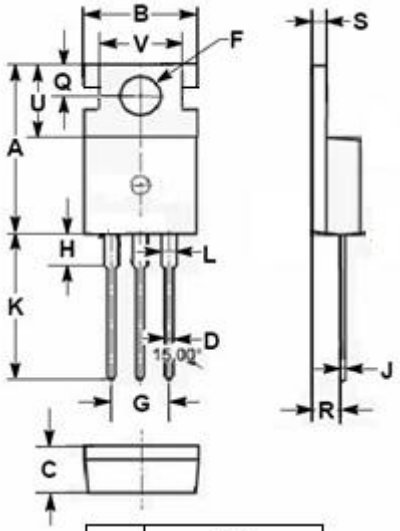
- Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= -60(V)(Min.)
- Complement to Type 2SC1985
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-6	A
I_B	Base Collector Current-Continuous	-3	A
P_C	Total Power Dissipation @ T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -25mA; I_B= 0	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-1.0	mA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -4V	40			
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A; V_{CE}= -12V		10		MHz
Switching Times						
t_r	Rise Time	I_C= -3A ,R_L= 3Ω , I_{B1}= -I_{B2}= -0.4A,V_{CC}= -9V		0.9		μs
t_{stg}	Storage Time			1.0		μs
t_f	Fall Time			0.1		μs